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Serial No.: 10/605,100

Art Unit: 2818

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7 December 2005

Date of Deposit

Graham S. Jones, II: Reg. No. 20,429

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7 December 2005

Date

### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventors:	Tina J. Wagner et al.	Date:	7 December 2005
Serial No.:	10/605,100	Art Unit:	2818
Filing Date:	09 September 2003	Examiner:	David Vu
Confirmation No.:	2099	Docket No.:	FIS920030249US1
Title:	A Raised Source Drain MOSFET with Notch Formed on Top of Gate Structure Filled with a Dielectric Plug	Attorney:	Graham S. Jones, II 42 Barnard Avenue Poughkeepsie, NY 12603-5023

### AMENDMENT AFTER FINAL REJECTION FILED WITH REQUEST FOR CONTINUED EXAMINATION (RCE) TRANSMITTAL

Mail Stop RCE  
Commissioner for Patents  
P.O. Box 1450  
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Your Honor:

In response to the Office Action of 8 November 2005, please amend the above-identified application as follows:

Amendments to the Abstract	begin on page 2 of this paper
Amendments to the Specification	begin on page 3 of this paper
Amendments to the Claims	begin on page 5 of this paper.
Remarks/Arguments	begin on page 10 of this paper.

FIS920030249US1

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